

FABRICATION OF GOLD NANODOT ON SILICON SUBSTRATE BY SCANNING PROBE MICROSCOPY AND ITS CHARACTERIZATION

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**UNIVERSITI SAINS MALAYSIA
2016**

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ITS CHARACTERIZATION**

by

TEGUH DARSONO

**Thesis submitted in fulfillment of the
requirements for the degree of
Doctor of Philosophy**

February 2016

ACKNOWLEDGMENTS

Bismillahirrohmanirrohim, in the Name of Alloh; the Most Gracious, the Most Merciful.

First, I would like to express my cordial gratitude to Almighty Alloh Subhanahu Wata'ala for guiding me to the righteous path of Islam and granting me to precious time until the fulfillment of my PhD in my pleasant university, USM. May the greetings and peace be upon our beloved Prophet Muhammad SAW.

I would like to thank to my main supervisor, Assoc. Prof. Dr. Sabar Derita Hutagalung, for continuous efforts in supervision, encouragement and all their help when I faced obstacles during my research. My gratitude also goes to my second supervisor, Prof. Dr. Zainal Arifin Ahmad, who has put all their his mind and the ability to assist me in everything, and also third supervisor, Assoc. Prof. Ir. Dr. Cheong Kuan Yew, a pleasure to give advice, suggestions and encouragement during my research.

I would also to thank to the School of Materials and Mineral Resources Engineering (SMMRE), USM for providing me adequate facilities and equipment since my first day of stepping the Electronics material laboratory. Thank you to all of academic and technical staff of SMMRE that I couldn't mention one by one for all their academic assistances. The Directorate General of Higher Education (DIKTI), Ministry of Education and Culture (Kemendikbud) of the Republic of Indonesia, for the award of a scholarship under the first batch (2008) of the overseas Postgraduates

Program. I would like to thank to the Rector UNNES who has given me permission to study and all their support that have been given.

I would like to express my sincere gratitude to all Indonesian students in USM, Dr. Janter P Simanjuntak, Dr. Samsudin Anis, Dr. Adhi Kusumastuti, Dr. Fathurrohman, Dr. Indra S Dalimunthe, Dr. Iping Suhariadi, Dr. Tedy Kurniawan, Faisal Budiman, M.Sc., Aris Warsita, M.T., Suriadi, M.Sc., Sahala Sialagan, M.Sc., Muh. Syukron, M.Eng., Dodi Ariawan, M.T, Sudibyoy, M.Sc., Miftah, M.Sc., Miss Mona, M.Sc., and Bapak Dr. Syafrudin Masri with his family.

Finally, I would like to express my regards to my beloved parents, almarhumah Sumiyatun and almarhum Suparwidodo; my beloved parents in law, Almarhum H. Mudjiono Dirdjo Sumarto and Hj. Mardinah, for their endless loves, concern and moral support, my beloved wife, Sri Kartikawati and all my dearest children, Aulia Fauziyyah Rahmi, M Khoirul Ihsan, Muflihanifah Fathurrahmi and also all my siblings, for their sacrifices and loves.

Teguh Darsono.

Desasiswa Utama, USM.

February, 2016.

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